

NCE P-Channel Enhancement Mode Power MOSFET

Description

The NCE60P17AQ uses advanced trench technology to provide excellent $R_{DS(ON)}$. This device is suitable for use as a load switch or power management.

Application

- Power management
- Load switch

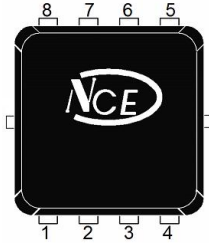
General Features

- $V_{DS} = -60V, I_D = -17A$
 $R_{DS(ON)} < 48m\Omega @ V_{GS} = -10V$
 $R_{DS(ON)} < 55m\Omega @ V_{GS} = -4.5V$
- High power and current handling capability
- Lead free product is acquired
- Surface mount package

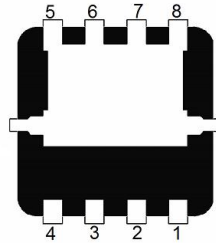
100% UIS TESTED!

100% ΔV_{ds} TESTED!

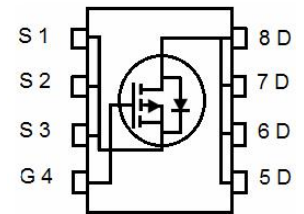
DFN 3.3X3.3



Top View



Bottom View



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE60P17AQ	NCE60P17AQ	DFN3.3X3.3-8L	-	-	-

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	-17	A
Drain Current-Continuous($T_C = 100^\circ C$)	$I_D (100^\circ C)$	-12	A
Pulsed Drain Current	I_{DM}	-68	A
Maximum Power Dissipation	P_D	32	W
Derating factor		0.26	W/ $^\circ C$
Single pulse avalanche energy (Note 5)	E_{AS}	55	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Case (Note 2)	$R_{\theta JC}$	3.9	$^\circ C/W$
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Electrical Characteristics ($T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
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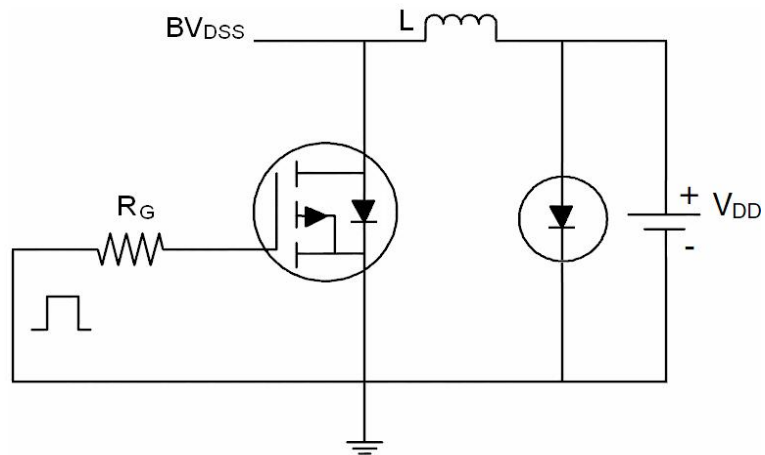
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA	-60	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-60V, V _{GS} =0V	-	-	-1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics <small>(Note 3)</small>						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-1	-1.5	-2.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-8A	-	40	48	mΩ
		V _{GS} =-4.5V, I _D =-8A	-	48	55	mΩ
Forward Transconductance	g _{FS}	V _{DS} =-5V, I _D =-8A	-	10	-	S
Dynamic Characteristics <small>(Note4)</small>						
Input Capacitance	C _{iss}	V _{DS} =-30V, V _{GS} =0V, F=1.0MHz	-	1630.7	-	PF
Output Capacitance	C _{oss}		-	90.6	-	PF
Reverse Transfer Capacitance	C _{rss}		-	77.3	-	PF
Switching Characteristics <small>(Note 4)</small>						
Turn-on Delay Time	t _{d(on)}	V _{DD} =-30V, R _L =1.5Ω, V _{GS} =-10V, R _G =3Ω	-	11	-	nS
Turn-on Rise Time	t _r		-	14	-	nS
Turn-Off Delay Time	t _{d(off)}		-	33	-	nS
Turn-Off Fall Time	t _f		-	13	-	nS
Total Gate Charge	Q _g	V _{DS} =-30, I _D =-8A, V _{GS} =-10V	-	30		nC
Gate-Source Charge	Q _{gs}		-	3.4		nC
Gate-Drain Charge	Q _{gd}		-	6.7		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage <small>(Note 3)</small>	V _{SD}	V _{GS} =0V, I _S =-8A	-		-1.2	V
Diode Forward Current <small>(Note 2)</small>	I _S		-	-	-17	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F =- 8A di/dt = -100A/μs ^(Note3)	-	34		nS
Reverse Recovery Charge	Q _{rr}		-	37		nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

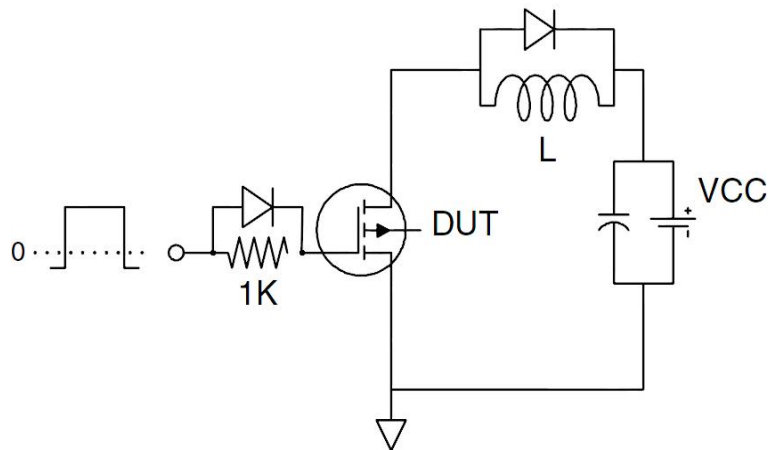
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. E_{AS} condition: $T_J=25^\circ C, V_{DD}=-30V, V_G=-10V, L=0.5mH, R_g=25\Omega$

Test Circuit

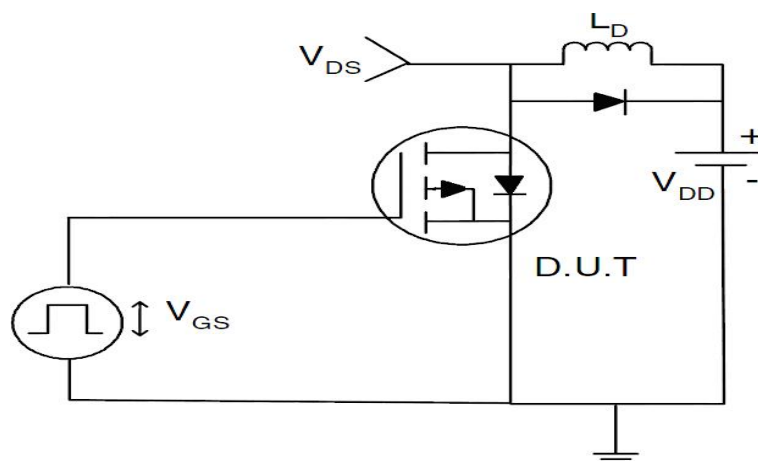
1) E_{AS} Test Circuit



2) Gate Charge Test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

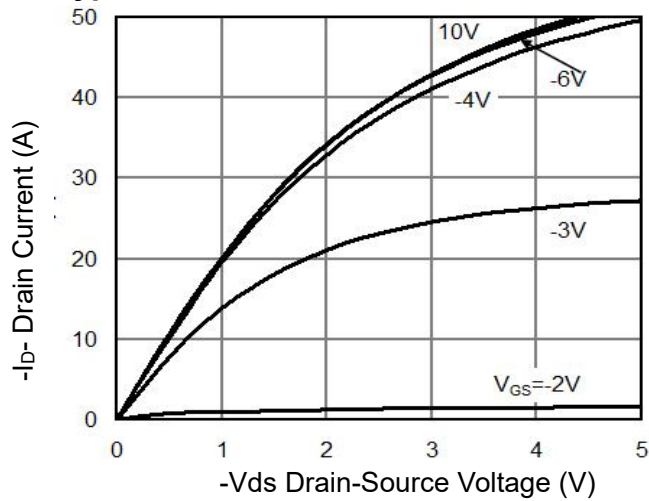


Figure 1 Output Characteristics

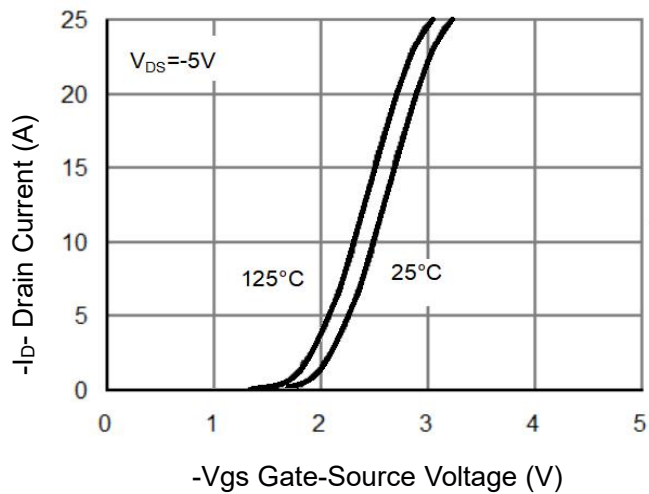


Figure 2 Transfer Characteristics

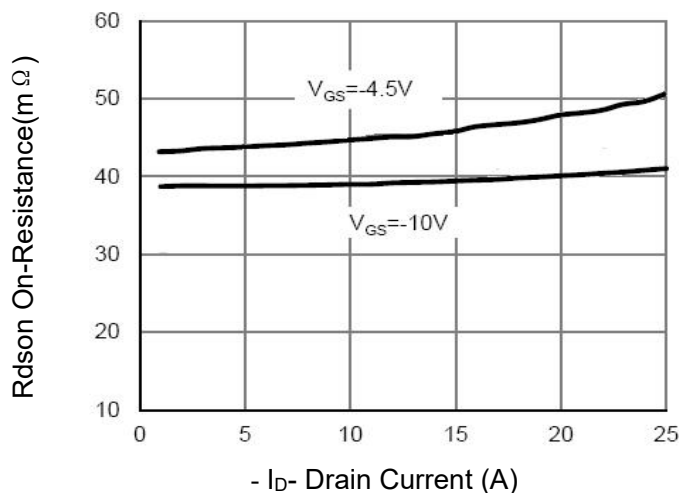


Figure 3 Rdson- Drain Current

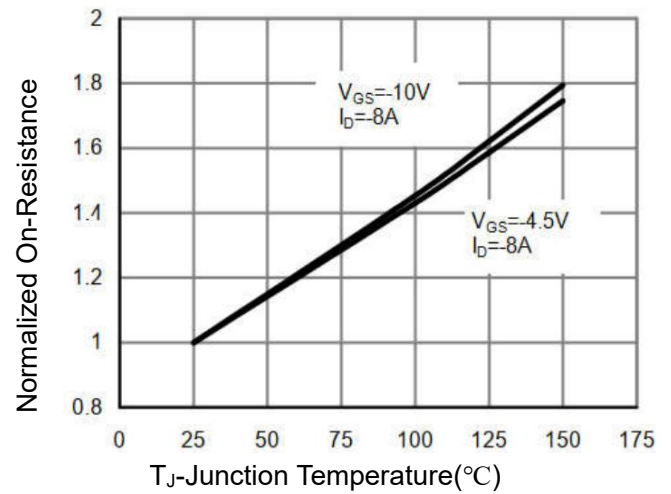


Figure 4 Rdson-Junction Temperature

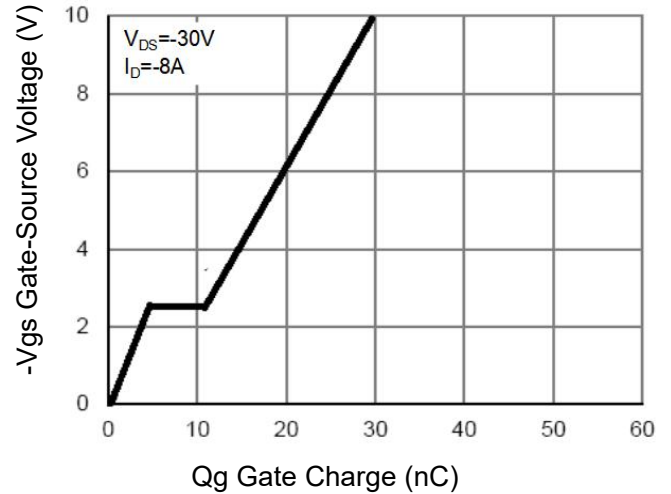


Figure 5 Gate Charge

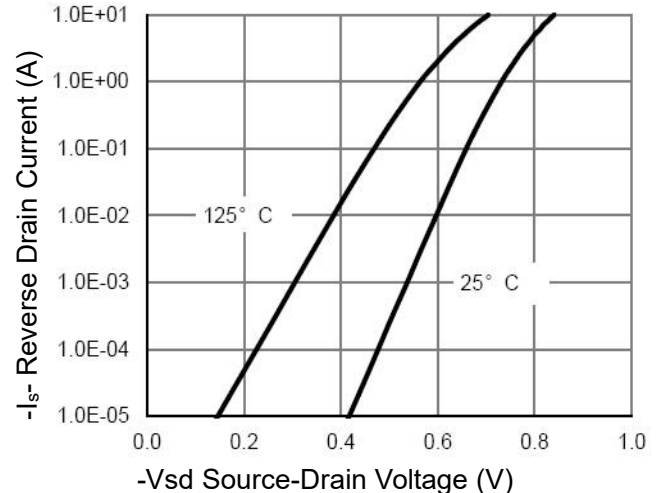


Figure 6 Source- Drain Diode Forward

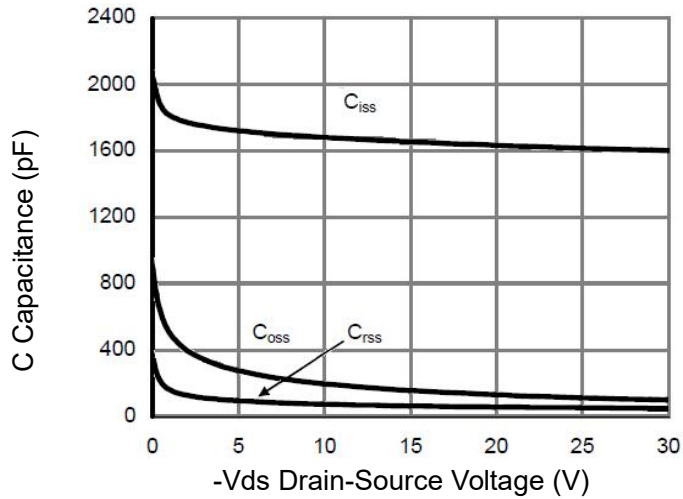


Figure 7 Capacitance vs Vds

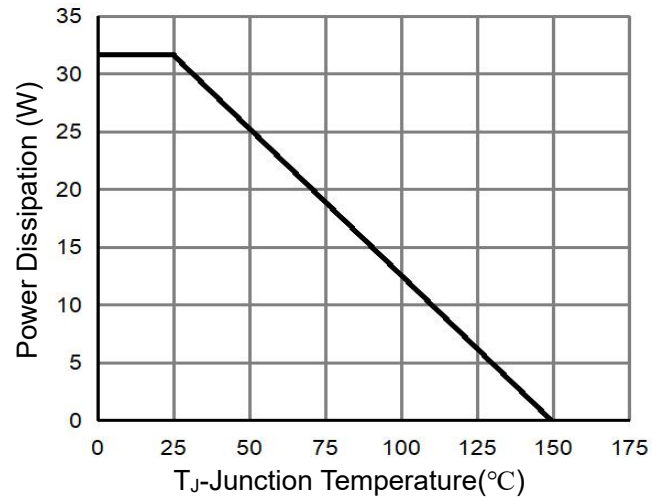


Figure 9 Power De-rating

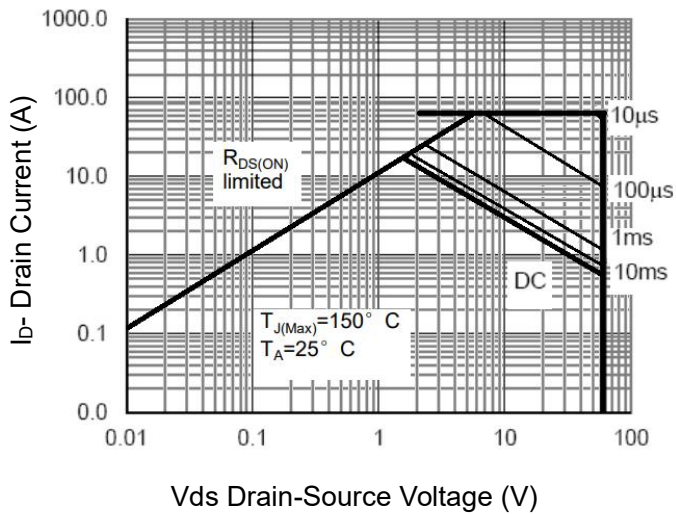


Figure 8 Safe Operation Area

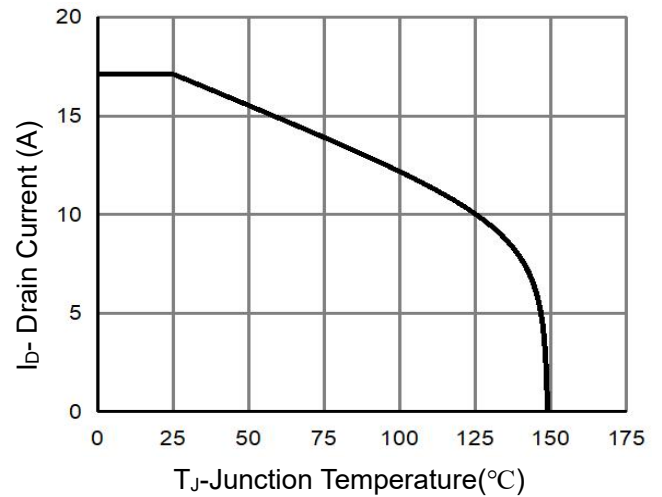


Figure 10 I_D Current De-rating

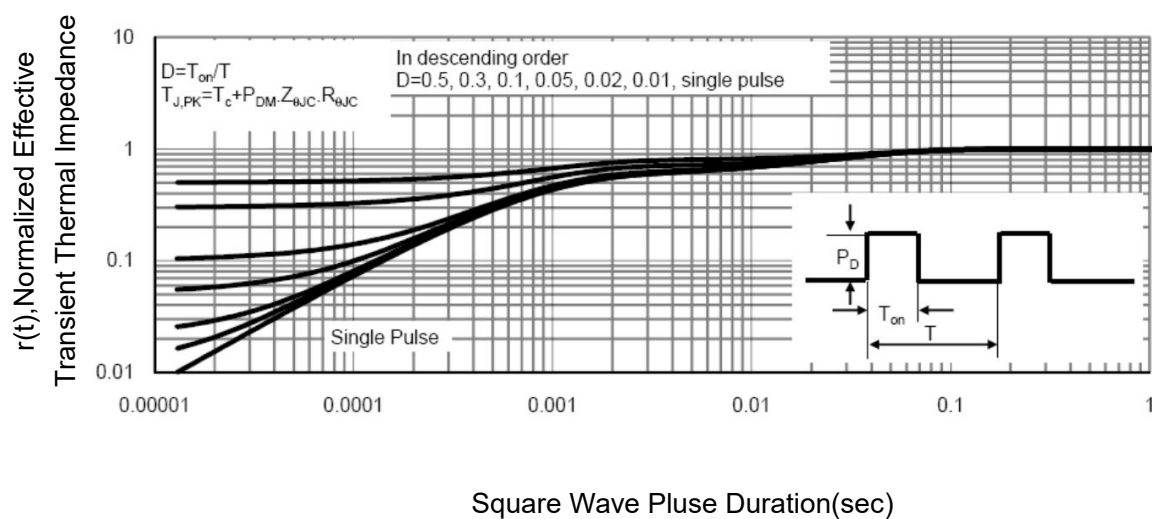
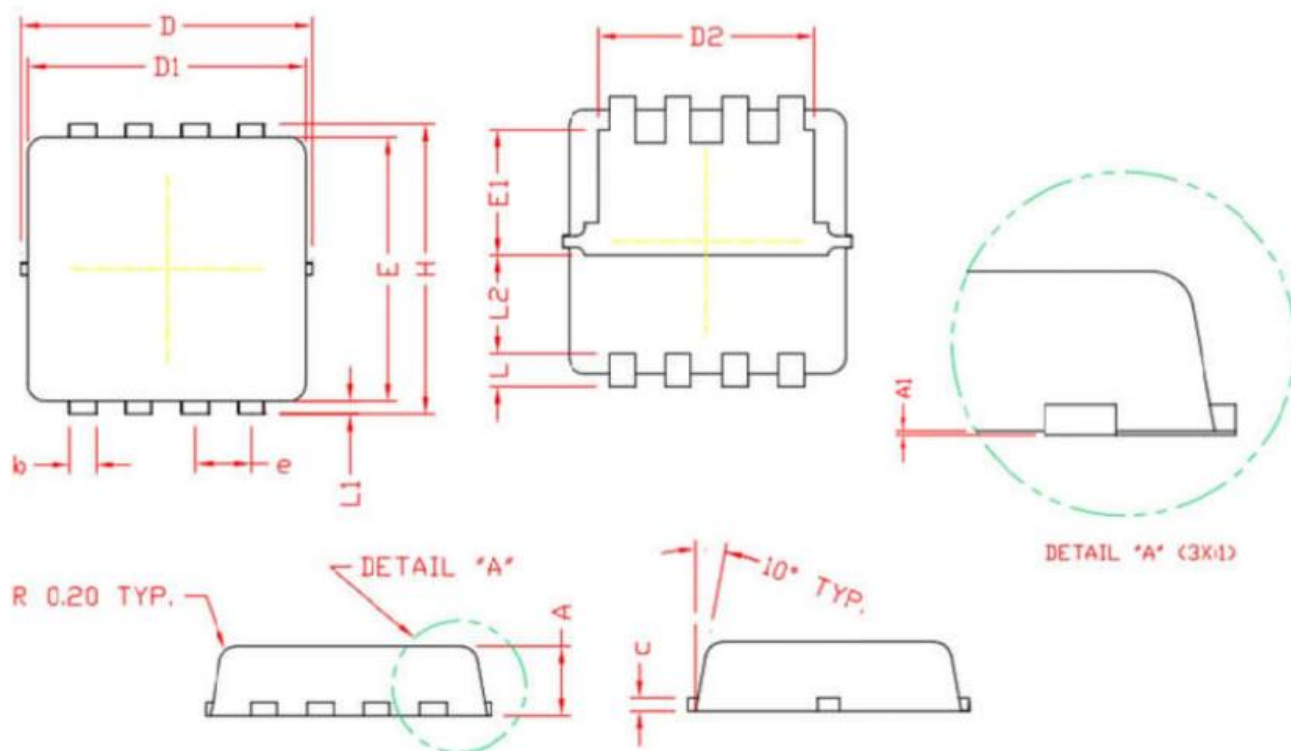


Figure 11 Normalized Maximum Transient Thermal Impedance

DFN3.3X3.3-8L Package Information



COMMON DIMENSIONS

(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	0.70	0.80	0.90
A1	0.00	0.03	0.05
b	0.24	0.30	0.35
c	0.10	0.15	0.20
D	3.25	3.32	3.40
D1	3.05	3.15	3.25
D2	2.40	2.50	2.60
E	3.00	3.10	3.20
E1	1.35	1.45	1.55
e	0.65 BSC.		
H	3.20	3.30	3.40
L	0.30	0.40	0.50
L1	0.10	0.15	0.20
L2	1.13 REF.		

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